Special Issue

Latest Progress in Wide Band-Gap Semiconductors

Message from the Guest Editors

Semiconductor material systems have now entered a new era, driven by demands stemming from accelerating advances in science and technology, which push forward the development of wide bandgap semiconductor materials and devices toward high power, low energy consumption, multiwavelength band, ultrafast response, miniaturization, and high integration degrees. The topics covered within this Special Issue include but are not limited to the following:

- The epitaxial growth of the wide band gap semiconductors (III-nitride semiconductors, SiC, ZnO, diamond, Ga2O3, etc.) and their low-dimensional quantum structures;
- Optical and electronic properties, doping and defects, structural analysis, and defect characterization;
- Optical devices such as micro-LEDs, VCSEL, edge emitting laser diodes, UV-LEDs, UV-laser diodes, single photon emitters, photodetectors, and intersubband emitters;
- Electronic devices for high power switching, high frequency, RF applications, etc.;
- Novel materials, nanostructures, and device concepts

Welcome to contribute.

Guest Editors

Prof. Dr. Ning Tang

Prof. Dr. Bo Shen

Dr. Liwen Sang

Dr. Guangxu Ju

Deadline for manuscript submissions

closed (1 January 2022)



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About the Journal

Message from the Editor-in-Chief

Electronics is a multidisciplinary journal designed to appeal to a diverse audience of research scientists, practitioners, and developers in academia and industry. The journal is devoted to fast publication of latest technological breakthroughs, cutting-edge developments, and timely reviews of current and emerging technologies related to the broad field of electronics. Experimental and theoretical results are published as regular peer-reviewed articles or as articles within Special Issues guest-edited by leading experts in selected topics of interest.

Editor-in-Chief

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manuscripts are peer-reviewed and a first decision is provided to authors approximately 16.8 days after submission; acceptance to publication is undertaken in 2.4 days (median values for papers published in this journal in the first half of 2025).

